

< C band internally matched power GaAs FET >

MGFC45V5964A

5.9 - 6.4 GHz BAND / 32W

DESCRIPTION

The MGFC45V5964A is an internally impedance-matched GaAs power FET especially designed for use in 5.9 - 6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Internally matched to 50(ohm) system

· High output power

P1dB=32W (TYP.) @f=5.9 - 6.4GHz

• High power gain

GLP=9dB (TYP.) @f=5.9 - 6.4GHz

• High power added efficiency

P.A.E.=33% (TYP.) @f=5.9 - 6.4GHz

• Low distortion [item -51]

IM3=-45dBc (Typ.) @Po=34.5dBm S.C.L

APPLICATION

• item 01: 5.9 - 6.4GHz band microwave high power amplifier

• item 51: 5.9 - 6.4GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=8A • RG=25ohm Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit				
VGDO	Gate to drain breakdown voltage	-15	V				
VGSO	Gate to source breakdown voltage	-15	V				
ID	Drain current	30	Α				
IGR	Reverse gate current	-80	mA				
IGF	Forward gate current	168	mA				
PT *1	Total power dissipation	150	W				
Tch	Cannel temperature	175	°C				
Tstg	Storage temperature	-65 to +175	°C				
*1 · Tc-25°C							

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (I) placement of substitutive, auxiliary circuits,

against any malfunction or mishap.

OUTLINE

R1.2±0.2

GF-38

Unit: mm

<u>H</u>

(1)gate

3drain

②source(frange)

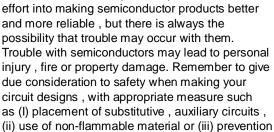
24±0.3

0.6±0.15

(3)

20.4±0.2

16.7±0.3



Keep Safety first in your circuit designs!

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	24	-	А
gm	Trans conductance	VDS=3V, ID=8A	-	8	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=160mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=8A	44.5	45	-	dBm
GLP *2	Linear Power Gain	f=5.9 – 6.4GHz	8	9	-	dB
P.A.E.	Power added efficiency	Pin=25dBm *2	-	33	-	%
ID	Drain current	1	-	8	-	А
IM3 *3	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *4	Thermal resistance	Delta Vf method	-	0.8	1	°C/W

^{*3 :}item -51, 2 tone test,Po=34.5dBm Single Carrier Level ,f=6.4GHz,delta f=10MHz

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^{*4 :}Channel-case

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